

Description

The DMTH3004LK3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.



TO-252-2L

General Features

V_{DS} = 30V I_D =120A

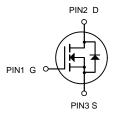
 $R_{DS(ON)}$ < 3.8 m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMTH3004LK3	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	30	V	
Vgs	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	in Current, V _{GS} @ 10V ¹ 120		
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	ntinuous Drain Current, V _{GS} @ 10V ¹ 75		
Ідм	Pulsed Drain Current ²	Pulsed Drain Current ² 384		
EAS	Single Pulse Avalanche Energy ³	196	mJ	
las	Avalanche Current	e Current 53.8		
P _D @T _C =25°C	Total Power Dissipation ⁴	62.5	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Reja	Thermal Resistance Junction-Ambient ¹	62	°C/W	



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Static Ch	aracteristics		Į.			
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	_
		T _J =85°C	-	-	30	μΑ
$V_{\rm GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	1.4	1.7	2.5	V
$I_{\rm GSS}$	Gate Leakage Current	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =20A	-	3	3.8	
$R_{\text{DS(ON)}}{}^{\text{d}}$		T _J =125°C	-	4.4	-	$m\Omega$
		V_{GS} =4.5V, I_{DS} =15A	-	4.0	5.5	
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =10A	-	24.6	-	S
Diode Ch	aracteristics					
V _{SD} d	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V	-	0.8	1.1	V
t _{rr}	Reverse Recovery Time		-	35.6	-	ns
t _a	Charge Time	1 =204 dl /dt=1004/	-	19.3	-	
t _b	Discharge Time	I_{DS} =20A, dI_{SD}/dt =100A/ μ s	-	16.3	-	
Q _{rr}	Reverse Recovery Charge		-	26	-	nC
Dynamic	Characteristics ^e					
R_{G}	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1	2	Ω
C _{iss}	Input Capacitance	V _{GS} =0V,	-	2485	2971	pF
C _{oss}	Output Capacitance	V _{DS} =15V,	-	850	-	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	85	-	
$t_{d(ON)}$	Turn-on Delay Time		-	12.4	23	ns
t _r	Turn-on Rise Time	V_{DD} =15V, R_{L} =15 Ω ,	-	9.5	18	
$t_{d(OFF)}$	Turn-off Delay Time	I_{DS} =1A, V_{GEN} =10V, R_{G} =6 Ω	-	27.2	49	
t _f	Turn-off Fall Time		-	35.2	64	
Gate Cha	rge Characteristics ^e			•	•	
Q_g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =20A	-	20.6	28.8	
Q_g	Total Gate Charge		-	9.8	-	
Q_{gth}	Threshold Gate Charge	V _{DS} =15V, V _{GS} =4.5V,	-	1.8	-	nC
Q_{gs}	Gate-Source Charge	I _{DS} =20A	-	3.8	-	
Q_{gd}	Gate-Drain Charge		-	3.7	-	

Note d : Pulse test ; pulse width≤300µs, duty cycle≤2%. Note e : Guaranteed by design, not subject to production testing.



Typical Operating Characteristics

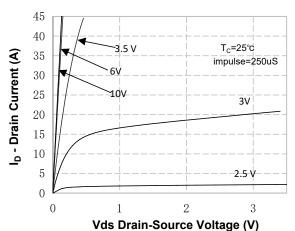


Figure 1. On-Region Characteristics

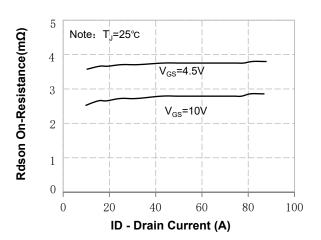


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

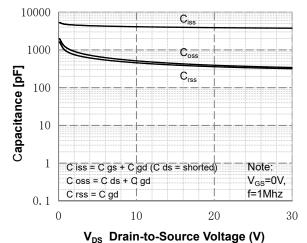


Figure 5. Capacitance Characteristics

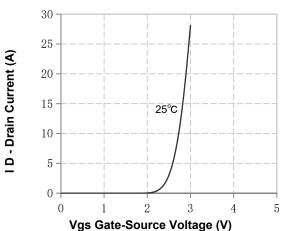


Figure 2. Transfer Characteristics

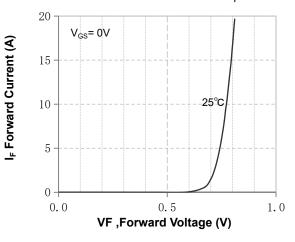


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

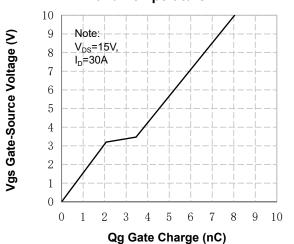
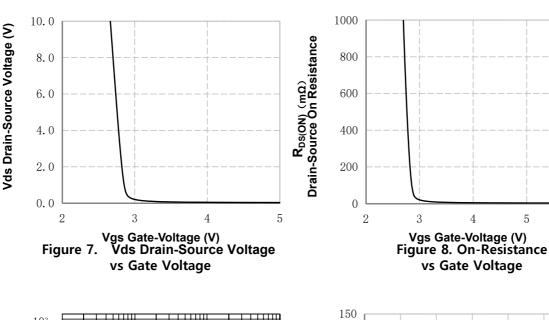
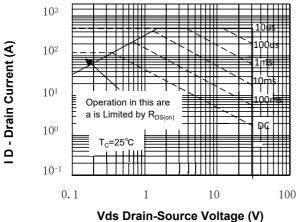


Figure 6. Gate Charge Characteristics





(Y) 100 100 50 0 25 50 75 100 125 150 T J -Junction Temperature(°C)

Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Continuous Drain Current vs Temperature

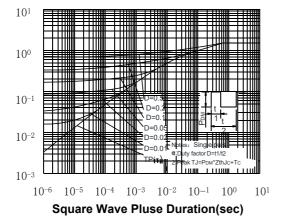
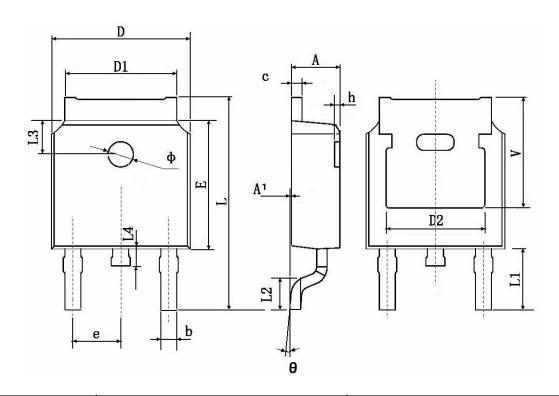


Figure 11. Transient Thermal Response Curve

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	5.350 TYP. 0.211 TYP.		TYP.	



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